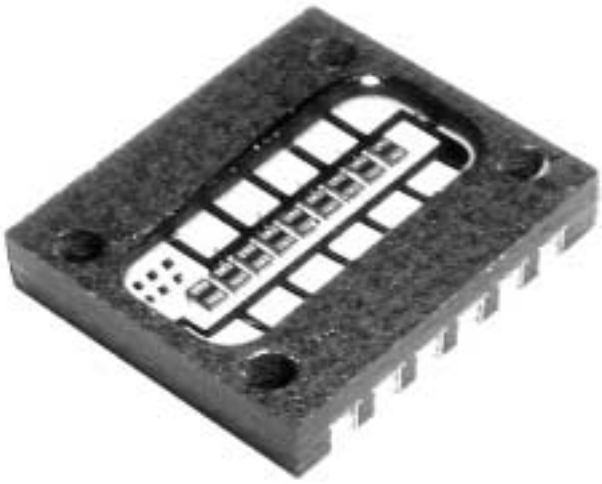
OL2009

9-Element SMD Phototransistor Array

Features

- **High speed phototransistor OL8110 chips**
- **Reference holes for precise mounting**
- **Compact size and low cost**
- **Also available with mounted reticle**
- **Custom design available**
- **Single chip placement for high speed applications**



Application

- **Optical Encoders (absolute, incremental, multi turn)**
- **Edge detection for paper**
- **Multi Element Sensor Array**

Absolute Maximum Ratings

Storage and Operating Temperature	-35 to +85 ºC (*)
Solder Temperature (Vapor Phase Reflow for 30 sec)	235 ºC

(*)Military Temperature range available on request

Electrical Specifications (T_A = 25ºC)

- Parameters 100% tested at waferprobe

Parameter	Units	Min	Typ	Max
I_{CE0} @ 52.0 V	µA		0.1	100.0
I_{DARK} @ 32.0 V	nA		1.0	100.0
I_{EC0} @ 7.7 V	µA		0.1	100.0
V_{CE}st (I_C = 2.0 mA, I_B = 22.2 µA)	mV		290.0	400.0
HFE (I_C = 2.0 mA, V_{CE} = 5.0 V)		500.0	750.0	1000.0

Additional Parameters tested for qualification and on a lot sample basis

- Rise time: 10.0 µs (V_{CC} = 5.0 V, R_L = 1.2 kΩ, C_L = 8.0 pF, V_E(peak) = 1.0 V)
- Fall time: 13.0 µs (V_{CC} = 5.0 V, R_L = 1.2 kΩ, C_L = 8.0 pF, V_E(peak) = 1.0 V)
- Responsitivity peak wavelength: 880 nm

Note

Please see part **ET8001**, precision schmitt trigger and comparator array with hysteresis tracking function for use with this phototransistor array.

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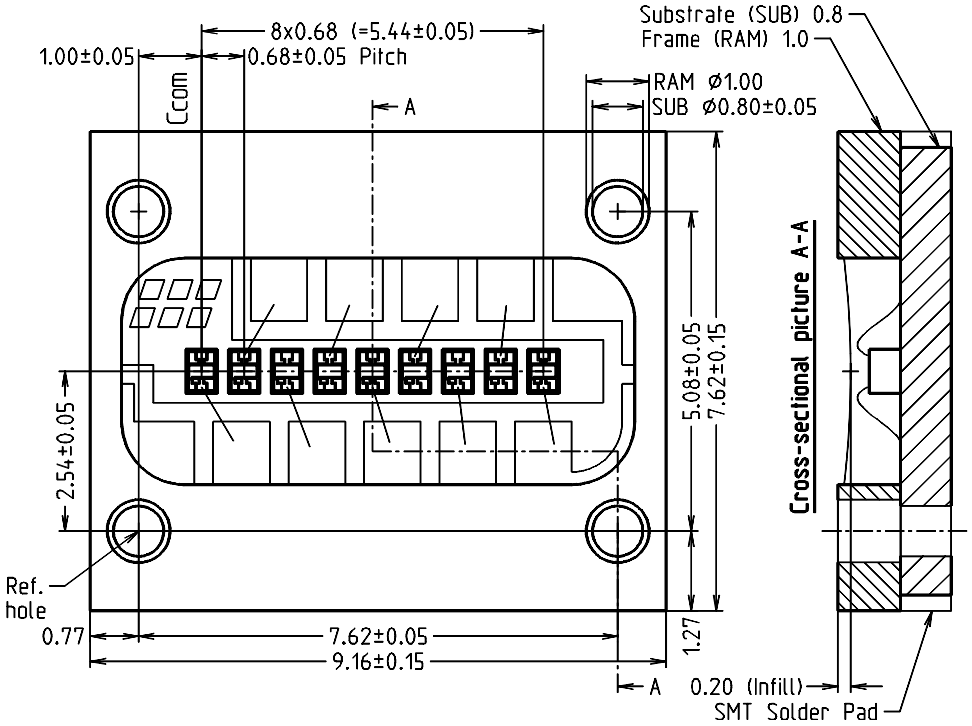
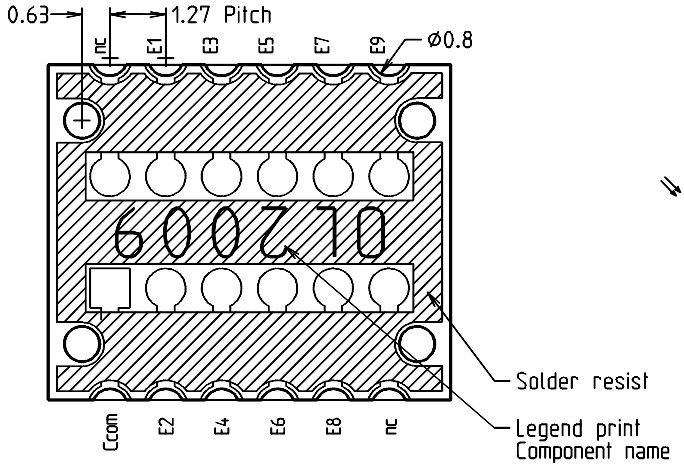
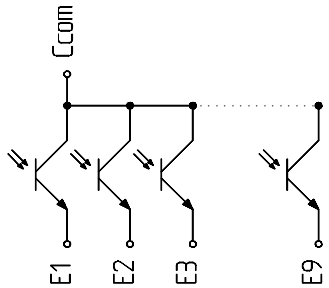
Top view



Bottom view

Chip type:
OL8110 (9x) Phototransistor
Chip thickness: 178µm - 254µm





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